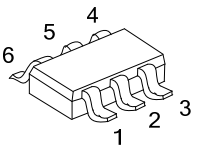
UH11K **Preliminary** ***NPN EPITAXIAL SILICON TRANSISTOR***

DUAL BIAS RESISTOR TRANSISTORS



SOT-363

■ DESCRIPTION

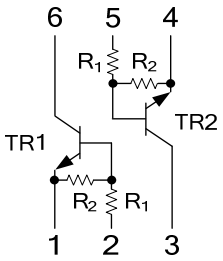
The UTC **UH11K** is a dual bias resistor transistors, it uses UTC's advanced technology to provide customers with saving board space, reducing component count, etc.

The UTC **UH11K** is suitable for low power surface mount applications, etc.

■ FEATURES

* Reducing component count
* Saving board space

■ EQUIVALENT CIRCUIT



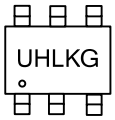
■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment						Packing
		1	2	3	4	5	6	
UH11KG-AL6-R	SOT-363	E1	B1	C2	E2	B2	C1	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UH11KG-AL6-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AL6: SOT-363 (3) G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Collector Current	I_C	100	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	-55~+150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=10μA, I_E=0	50			V
Collector-Emitter Breakdown Voltage (Note 1)	BV_{CEO}	I_C=2.0mA, I_B=0	50			V
Collector-Base Cutoff Current	I_{CBO}	V_{CB}=50V, I_E=0			100	nA
Collector-Emitter Cutoff Current	I_{CEO}	V_{CE}=50V, I_B=0			500	nA
Emitter-Base Cutoff Current	I_{EBO}	V_{EB}=6.0V, I_C=0			0.5	mA
ON CHARACTERISTICS (Note 2)						
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=5.0mA	35	60		
Output Voltage (on)	V_{OL}	V_{CC}=5.0V, V_B=2.5V, R_L=1.0 kΩ			0.2	V
ON CHARACTERISTICS (Note 2)						
Input Resistor	R_1		7.0	10	13	kΩ
Resistor Ratio	R_1/R_2		0.8	1.0	1.2	kΩ

Notes: 1. Pulse Test: Pulse Width<300μs, Duty Cycle<2.0%
2. Pulse Test: Pulse Width<300ms, Duty Cycle<2.0%